

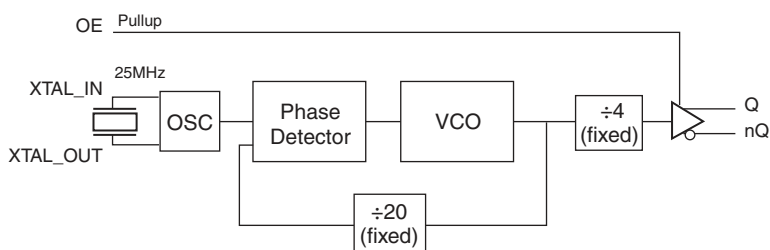
General Description

The 843021I-01 is a Gigabit Ethernet Clock Generator. The 843021I-01 uses a 25MHz crystal to synthesize 125MHz. The 843021I-01 has excellent phase jitter performance, over the 1.875MHz – 20MHz integration range. The 843021I-01 is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

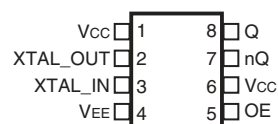
Features

- One differential 3.3V or 2.5V LVPECL output
- Crystal oscillator interface designed for 25MHz, 18pF parallel resonant crystal
- Output frequency range: 125MHz, using a 25MHz crystal
- VCO range: 490MHz – 640MHz
- RMS phase jitter @ 125MHz, using a 25MHz crystal (1.875MHz – 20MHz): 0.41ps (typical)
- Full 3.3V or 2.5V operating supply
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram



Pin Assignment



843021I-01

8 Lead TSSOP

4.40mm x 3.0mm x 0.925mm package body

G Package

Top View

Table 1. Pin Descriptions

Number	Name	Type		Description
1, 6	V _{CC}	Power		Power supply pins.
2, 3	XTAL_OUT XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.
4	V _{EE}	Power		Negative supply pin.
5	OE	Input	Pullup	Active high output enable. When logic HIGH, the outputs are enabled and active. When logic LOW, the outputs are disabled and are in a high impedance state. LVCMOS/LVTTL interface levels.
7, 8	nQ, Q	Output		Differential output pair. LVPECL interface levels.

NOTE: Pullup refers to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		kΩ

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V _{CC}	4.6V
Inputs, V _I	-0.5V to V _{CC} + 0.5V
Outputs, I _O Continuous Current Surge Current	50mA 100mA
Package Thermal Impedance, θ _{JA}	129.5°C/W (0 mps)
Storage Temperature, T _{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 3A. Power Supply DC Characteristics, V_{CC} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{CC}	Positive Supply Voltage		3.135	3.3	3.465	V
I _{EE}	Power Supply Current				64	mA

Table 3B. Power Supply DC Characteristics, V_{CC} = 2.5V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{CC}	Positive Supply Voltage		2.375	2.5	2.625	V
I _{EE}	Power Supply Current				62	mA

Table 3C. LVCMOS/LVTTL DC Characteristics, $V_{CC} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $V_{EE} = 0V$, $T_A = 0^\circ C$ to $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	$V_{CC} = 3.3V$	2		$V_{CC} + 0.3$	V
		$V_{CC} = 2.5V$	1.7		$V_{CC} + 0.3$	V
V_{IL}	Input Low Voltage	$V_{CC} = 3.3V$	-0.3		0.8	V
		$V_{CC} = 2.5V$	-0.3		0.7	V
I_{IH}	Input High Current	$V_{CC} = V_{IN} = 3.465$ or $2.625V$			5	μA
I_{IL}	Input Low Current	$V_{CC} = 3.465V$ or $2.625V$, $V_{IN} = 0V$	-150			μA

Table 3D. LVPECL DC Characteristics, $V_{CC} = 3.3V \pm 5\%$, $V_{EE} = 0V$, $T_A = -40^\circ C$ to $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		$V_{CC} - 1.4$		$V_{CC} - 0.9$	V
V_{OL}	Output Low Voltage; NOTE 1		$V_{CC} - 2.0$		$V_{CC} - 1.7$	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.0	V

NOTE 1: Outputs termination with 50Ω to $V_{CC} - 2V$.**Table 3E. LVPECL DC Characteristics, $V_{CC} = 2.5V \pm 5\%$, $V_{EE} = 0V$, $T_A = -40^\circ C$ to $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		$V_{CC} - 1.4$		$V_{CC} - 0.9$	V
V_{OL}	Output Low Voltage; NOTE 1		$V_{CC} - 2.0$		$V_{CC} - 1.5$	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.4		1.0	V

NOTE 1: Outputs termination with 50Ω to $V_{CC} - 2V$.**Table 4. Crystal Characteristics**

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency; NOTE 1			25		MHz
Equivalent Series Resistance (ESR)				90	Ω
Shunt Capacitance				7	pF
Drive Level				300	μW

AC Electrical Characteristics

Table 5A. AC Characteristics, $V_{CC} = 3.3V \pm 5\%$, $V_{EE} = 0V$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency		122.5	125	160	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter, Random; NOTE 1	125MHz, (Integration Range: 1.875MHz – 20MHz)		0.41		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	250		600	ps
odc	Output Duty Cycle		49		51	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions

NOTE 1: Please refer to Phase Noise Plot.

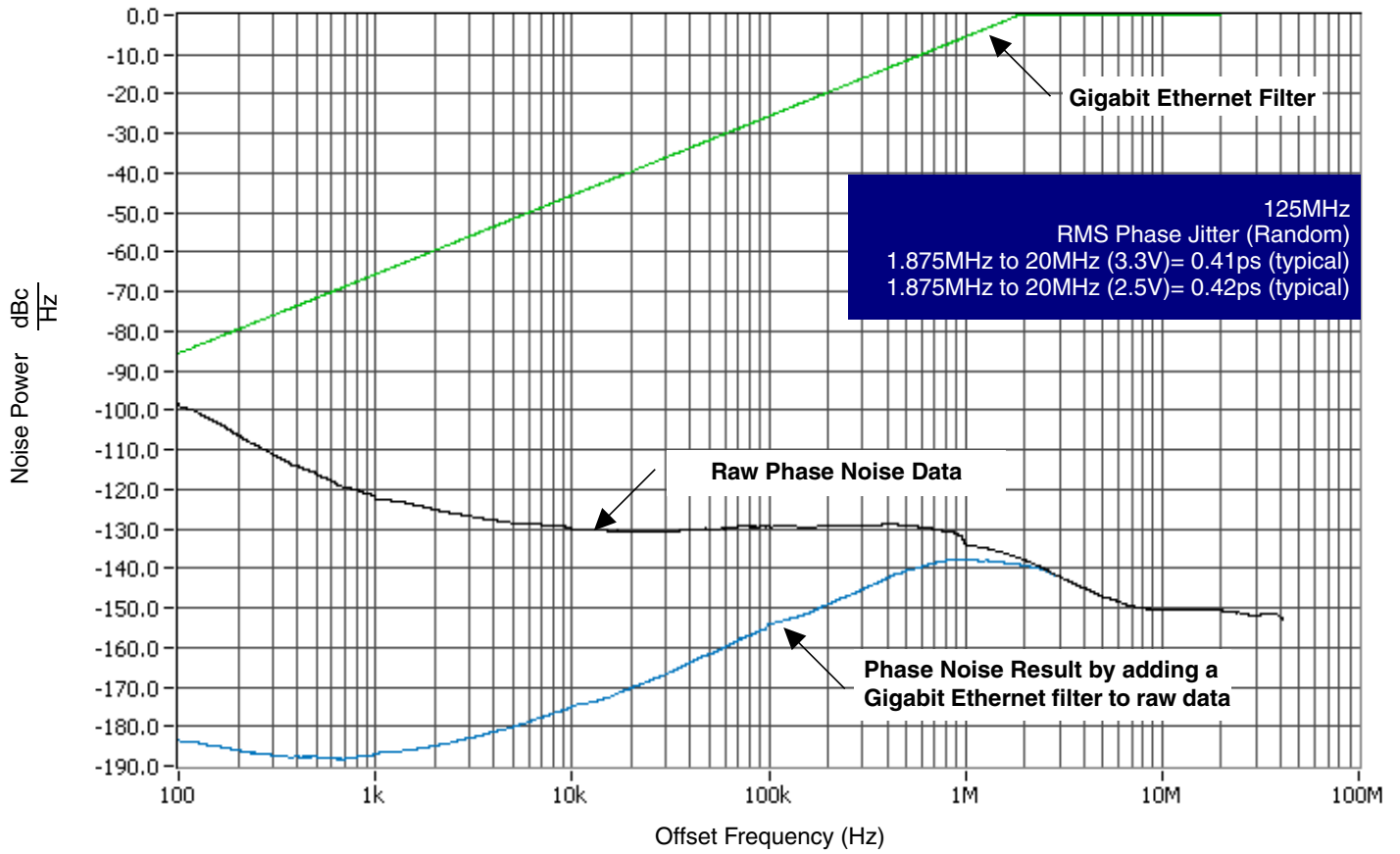
Table 5B. AC Characteristics, $V_{CC} = 2.5V \pm 5\%$, $V_{EE} = 0V$, $T_A = -40^\circ\text{C}$ to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency		122.5	125	160	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter, Random; NOTE 1	125MHz, (Integration Range: 1.875MHz – 20MHz)		0.42		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	250		600	ps
odc	Output Duty Cycle		49		51	%

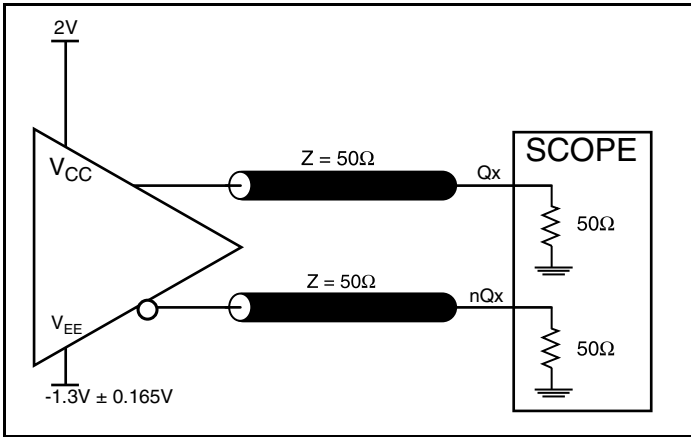
NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions

NOTE 1: Please refer to Phase Noise Plot.

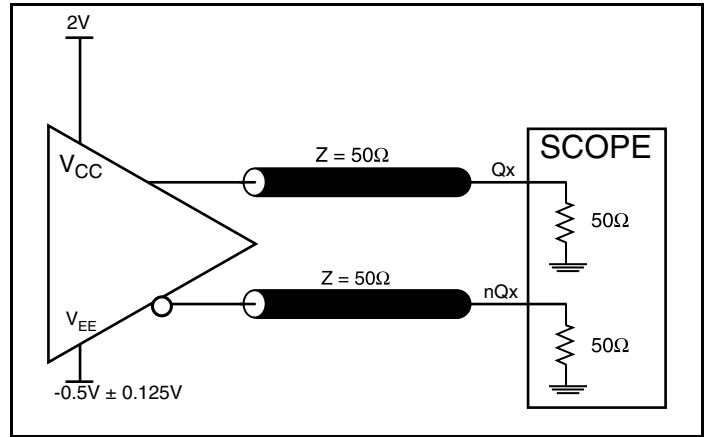
Typical Phase Noise at 125MHz (3.3V or 2.5V)



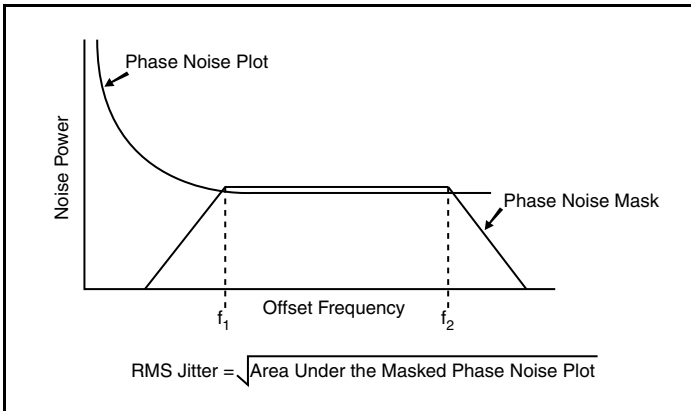
Parameter Measurement Information



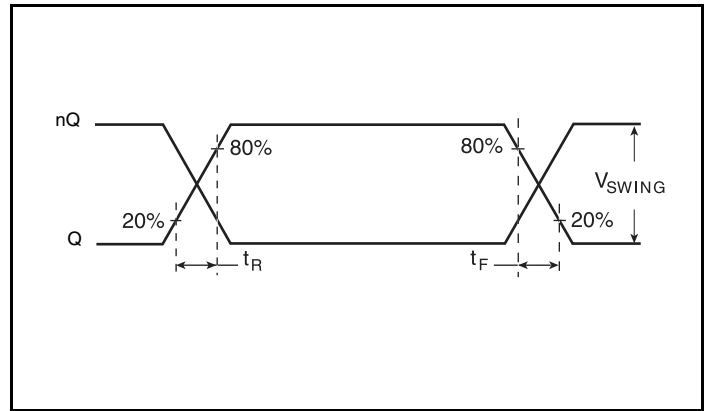
3.3V LVPECL Output Load AC Test Circuit



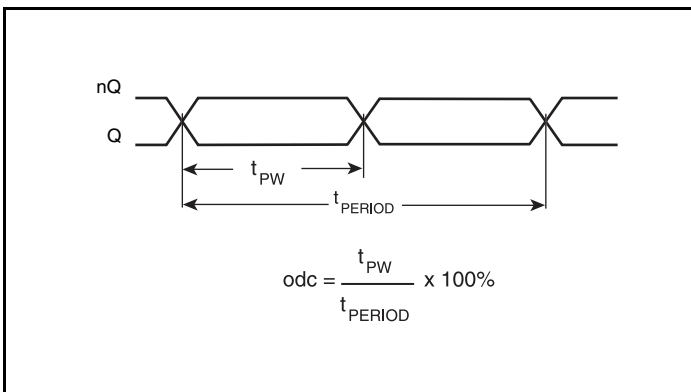
2.5V LVPECL Output Load AC Test Circuit



RMS Phase Jitter



Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period

Applications Information

Crystal Input Interface

The 8430211-01 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 1* below were determined using a 25MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

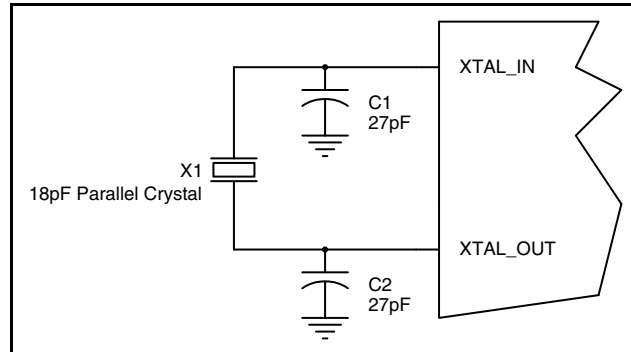


Figure 1. Crystal Input Interface

Overdriving the XTAL Interface

The XTAL_IN input can accept a single-ended LVCMOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 2A*. The XTAL_OUT pin can be left floating. The maximum amplitude of the input signal should not exceed 2V and the input edge rate can be as slow as 10ns. This configuration requires that the output impedance of the driver (R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition,

matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50Ω applications, R1 and R2 can be 100Ω. This can also be accomplished by removing R1 and making R2 50Ω. By overdriving the crystal oscillator, the device will be functional, but note, the device performance is guaranteed by using a quartz crystal.

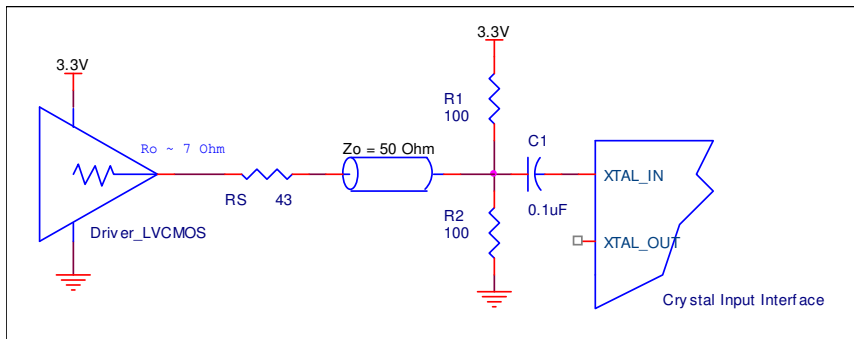


Figure 2A. General Diagram for LVCMOS Driver to XTAL Input Interface

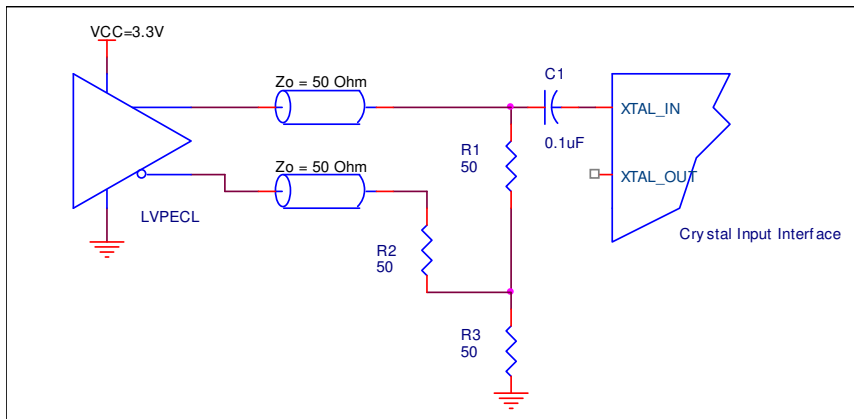


Figure 2B. General Diagram for LVPECL Driver to XTAL Input Interface

Termination for 3.3V LVPECL Outputs

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive 50Ω

transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion.

Figures 3A and 3B show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

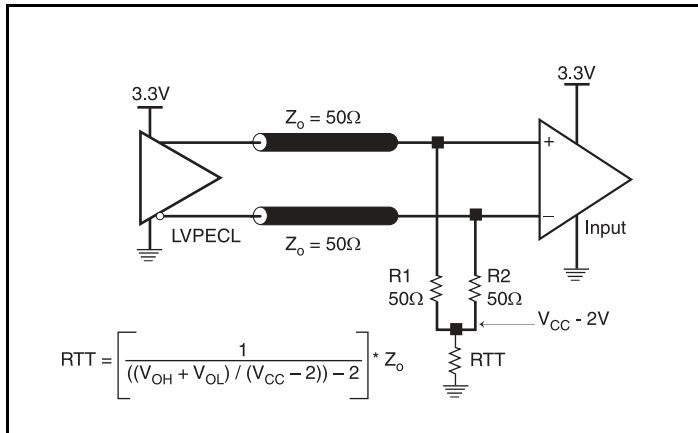


Figure 3A. 3.3V LVPECL Output Termination

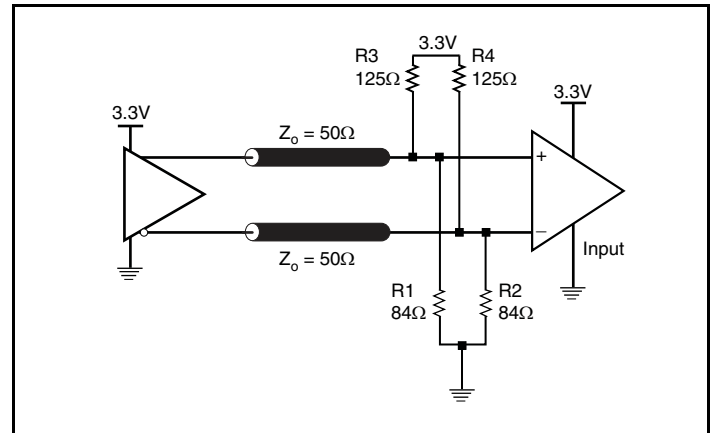


Figure 3B. 3.3V LVPECL Output Termination

Termination for 2.5V LVPECL Outputs

Figure 4A and Figure 5B show examples of termination for 2.5V LVPECL driver. These terminations are equivalent to terminating 50Ω to $V_{CC} - 2V$. For $V_{CC} = 2.5V$, the $V_{CC} - 2V$ is very close to

ground level. The R3 in Figure 4B can be eliminated and the termination is shown in Figure 4C.

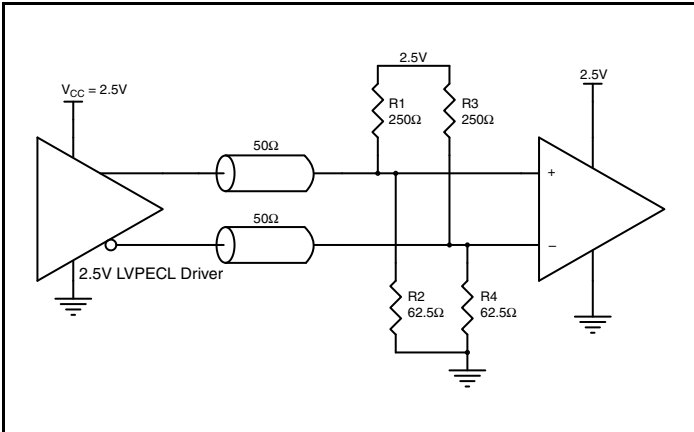


Figure 4A. 2.5V LVPECL Driver Termination Example

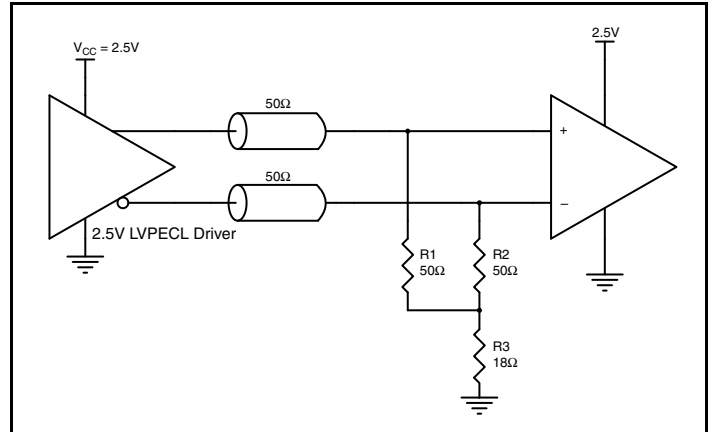


Figure 4B. 2.5V LVPECL Driver Termination Example

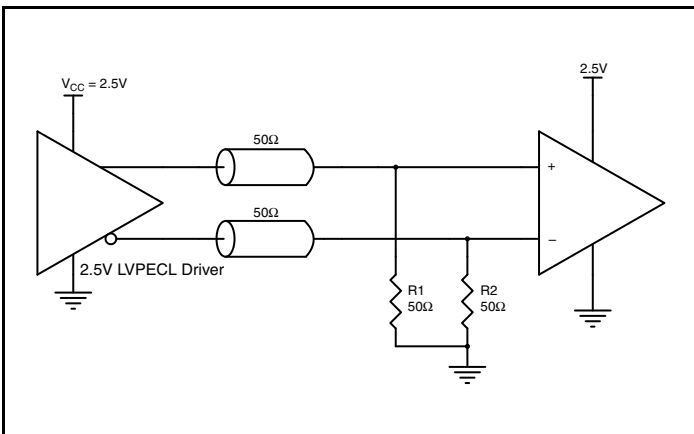


Figure 4C. 2.5V LVPECL Driver Termination Example

Schematic Example

Figure 5 shows an example of 8430211-01 application schematic. In this example, the device is operated at $V_{CC} = 3.3V$. The decoupling capacitor should be located as close as possible to the power pin. The input is driven by a 25MHz quartz crystal. For the LVPECL output

drivers, only two termination examples are shown in this schematic. Additional termination approaches are shown in the LVPECL Termination Application Note.

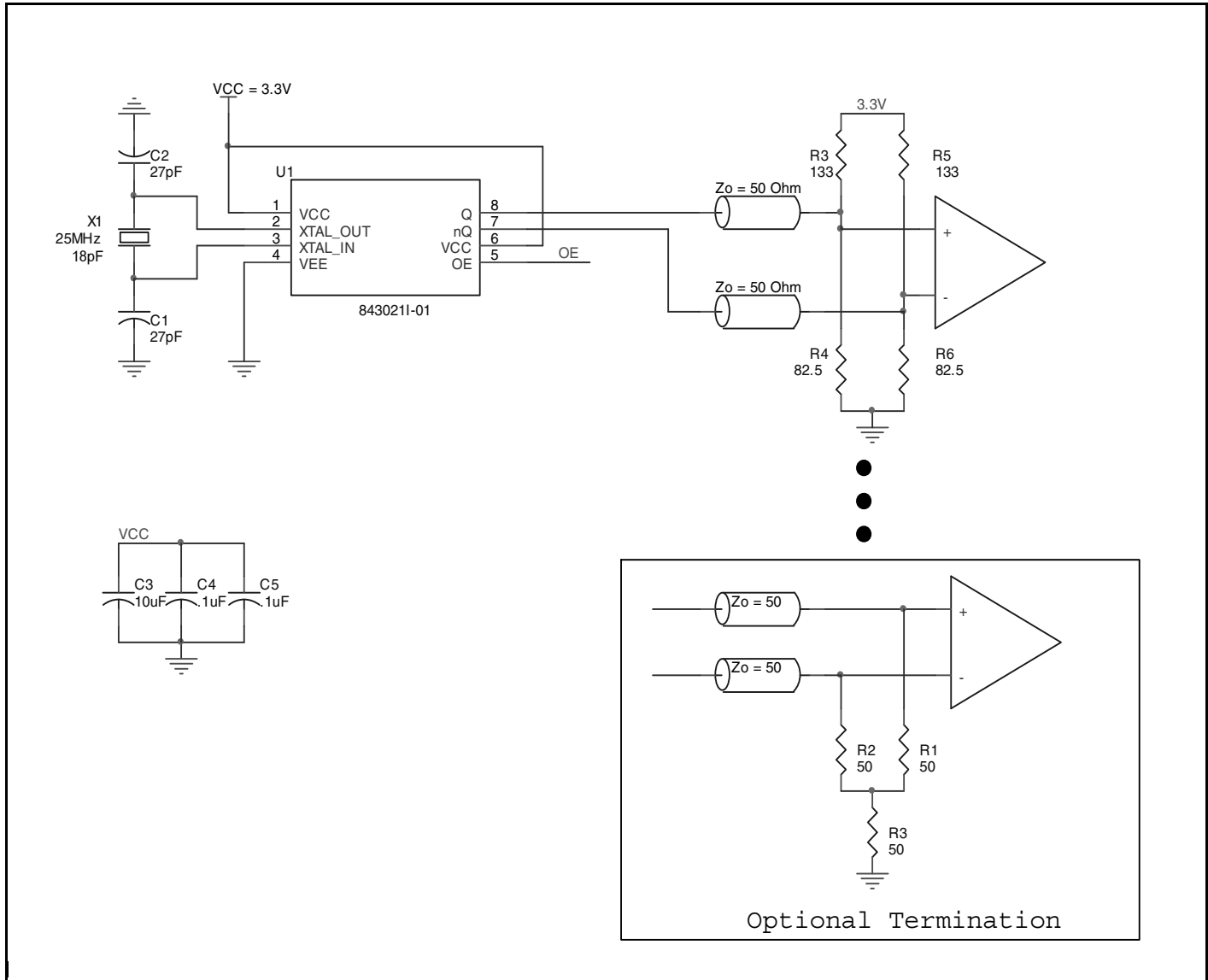


Figure 5. 8430211-01 Schematic Example

Power Considerations

This section provides information on power dissipation and junction temperature for the 843021I-01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 843021I-01 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{CC} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{CC_MAX} * I_{EE_MAX} = 3.465V * 64mA = \mathbf{221.76mW}$
- Power (outputs)_{MAX} = **30mW/Loaded Output pair**

Total Power_{MAX} (3.465V, with all outputs switching) = 221.76mW + 30mW = **251.76mW**

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 129.5°C/W per Table 6 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.252\text{W} * 90.5^\circ\text{C/W} = 117.6^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 8 Lead TSSOP, Forced Convection

θ_{JA} by Velocity			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	129.5°C/W	125.5°C/W	123.5°C/W

3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

LVPECL output driver circuit and termination are shown in *Figure 6*.

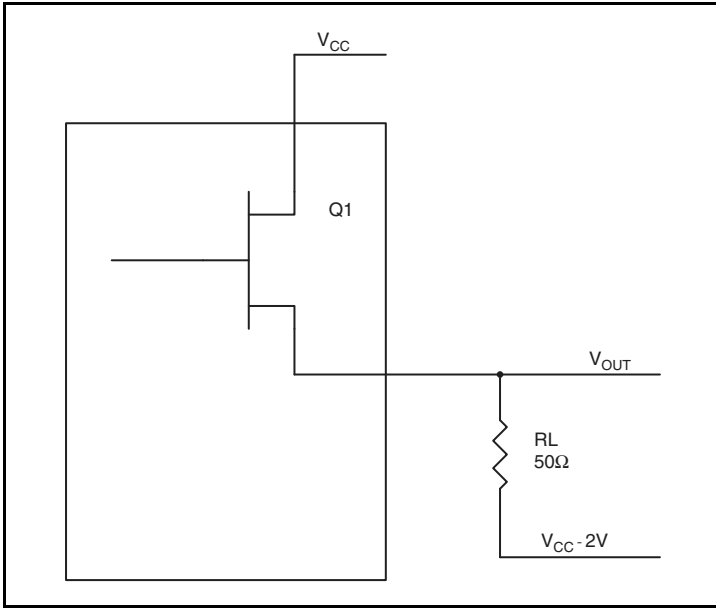


Figure 6. LVPECL Driver Circuit and Termination

To calculate worst case power dissipation into the load, use the following equations which assume a 50Ω load, and a termination voltage of $V_{CC} - 2V$.

- For logic high, $V_{OUT} = V_{OH_MAX} = V_{CC_MAX} - 0.9V$
($V_{CC_MAX} - V_{OH_MAX}$) = **0.9V**
- For logic low, $V_{OUT} = V_{OL_MAX} = V_{CC_MAX} - 1.7V$
($V_{CC_MAX} - V_{OL_MAX}$) = **1.7V**

Pd_H is power dissipation when the output drives high.

Pd_L is the power dissipation when the output drives low.

$$Pd_H = [(V_{OH_MAX} - (V_{CC_MAX} - 2V))/R_L] * (V_{CC_MAX} - V_{OH_MAX}) = [(2V - (V_{CC_MAX} - V_{OH_MAX}))/R_L] * (V_{CC_MAX} - V_{OH_MAX}) = [(2V - 0.9V)/50\Omega] * 0.9V = \mathbf{19.8mW}$$

$$Pd_L = [(V_{OL_MAX} - (V_{CC_MAX} - 2V))/R_L] * (V_{CC_MAX} - V_{OL_MAX}) = [(2V - (V_{CC_MAX} - V_{OL_MAX}))/R_L] * (V_{CC_MAX} - V_{OL_MAX}) = [(2V - 1.7V)/50\Omega] * 1.7V = \mathbf{10.2mW}$$

Total Power Dissipation per output pair = $Pd_H + Pd_L = \mathbf{30mW}$

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 8 Lead TSSOP

θ_{JA} vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	129.5°C/W	125.5°C/W	123.5°C/W

Transistor Count

The transistor count for 8430211-01 is: 1765

Package Outline and Package Dimensions

Package Outline - G Suffix for 8 Lead TSSOP

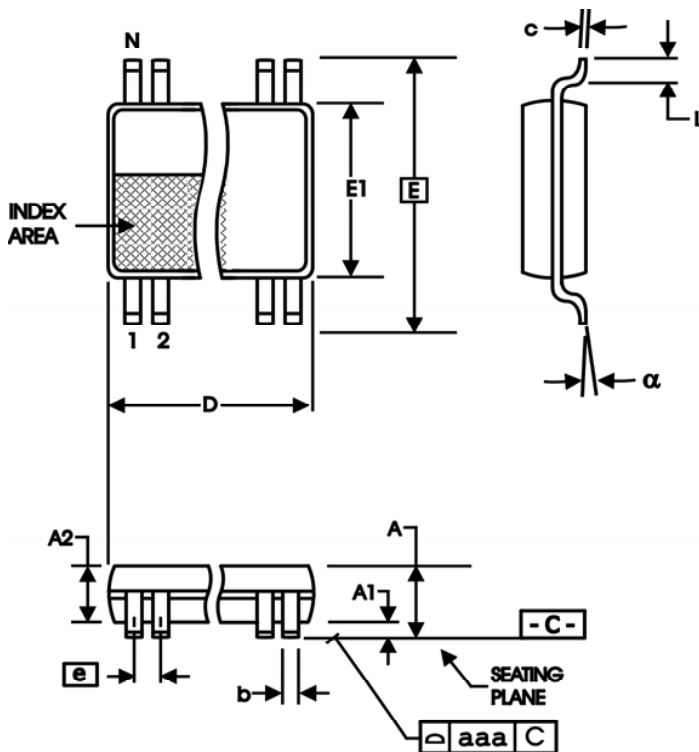


Table 8. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	8	
A		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	2.90	3.10
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
843021AGI-01LF	AI01L	"Lead-Free" 8 Lead TSSOP	Tube	-40°C to 85°C
843021AGI-01LFT	AI01L	"Lead-Free" 8 Lead TSSOP	Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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Revision History Sheet

Rev	Table	Page	Description of Change	Date
A	T9	14	Ordering Information Table - corrected "Temperature" column.	5/14/08
A	T1	2	Pin Description Table - corrected typo in V_{CC} row, pins 1, 6 instead of 1, 8.	11/10/08
A	T3D - T3E	3 7	LVPECL DC Characteristics Tables - corrected V_{OH}/V_{OL} parameters from "Current" to "Voltage" and units from "uA" to "V". Updated "Overdriving the Crystal Interface" section. Updated header/footer.	10/15/10
A	T9	14	Ordering Information - removed leaded devices.	9/25/15



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